

Topics of Applied Solid State Physics (2019)

1. Band structure picture of solids. Methods for calculating energy bands (nearly free electron model, tight binding model), electronic bands in crystals in 1, 2 and 3 dimensions for different valence numbers (1, 2 and higher); metals, semiconductors, insulators; limitations of band structure picture.

(*S. H. Simon: The Oxford Solid State Basics, sections 16.1–16.4.*)

2. Band structure and optical properties. Optical excitations in insulators and semiconductors, relation of color and band gap, direct and indirect transitions, energy and momentum conservation; optical excitations in metals (reflectance, color); optical effects of impurities.

(*S. H. Simon: The Oxford Solid State Basics, section 16.5.*)

3. Semiconductor physics I. Electrons and holes, effective mass approximation, momentum and velocity of a hole; quasiclassical equation of motion, Drude transport, mobility.

(*S. H. Simon: The Oxford Solid State Basics, section 17.1.*)

4. Semiconductor physics II. Intrinsic and extrinsic semiconductors, the effect of doping; donors and acceptors in Si, impurity states, estimation of binding energy; impurity eigenstates.

(*S. H. Simon: The Oxford Solid State Basics, section 17.2.*)

5. Semiconductor physics III. Statistical mechanics of semiconductors: density of states, exponential activation, law of mass action, density of conduction electrons and holes in intrinsic and extrinsic semiconductors; conductivity of doped semiconductors as a function of temperature.

(*S. H. Simon: The Oxford Solid State Basics, section 17.3.*)

6. Semiconductor devices I. Band structure engineering, semiconductor heterostructures, modulation doping and 2DEG, the unbiased p - n junction, estimation of width of depletion region, electrochemical potential, solar cells and photodiodes.

(*S. H. Simon: The Oxford Solid State Basics, sections 18.1–18.2.*)

7. Semiconductor devices II. Biased p - n junction: the diode, calculating the $I(V)$ characteristics, simplified model, rectification; the transistor, operating principle of a MOSFET.

(*S. H. Simon: The Oxford Solid State Basics, sections 18.2–18.3.*)

8. Charge transport in mesoscopic systems. Moore's law, new phenomena at nanoscale; equations of classical diffusive transport, Drude picture; characteristic lengthscales and timescales, typical values in metals and 2DEG; ballistic vs. diffusive regime; resistance of a nanowire, Landauer formalism, conductance quantization.

([e-learning material no. 1.](#))

9. Thermoelectric transport in mesoscopic systems. Bethe-Sommerfeld expansion (motivation). Thermoelectric phenomena: Seebeck effect, heat current, Wiedemann-Franz law, Peltier effect, Kelvin's formula.

([e-learning material no. 2.](#))

10. Coherent and incoherent transport. Four probe resistance, coherent and incoherent serial connection of scattering centers, transmission and reflection probabilities, demonstration of Ohm's law.

([e-learning material no. 3.](#))

11. The Boltzmann equation I. Equilibrium and non-equilibrium distribution functions, derivation of Boltzmann equation without collisions, Liouville's theorem; effect of collisions, incoming and outgoing flux.

([e-learning material no. 4. - Hungarian](#))

12. The Boltzmann equation II. Relaxation time approximation, solution in uniform E -field (without temperature gradient); conductivity of empty, fully filled and partially filled band; conductivity of an isotropic system, application for parabolic dispersion (Drude's result); temperature dependence of resistivity of metals, Mathiessen rule.

([e-learning material no. 4. - Hungarian](#))

13. The Boltzmann equation III. Solution in the presence of E -field and temperature/chemical potential gradient; application: thermoelectric effects, heat conductance, Seebeck coefficient, Peltier coefficient, Kelvin's relation.

([e-learning material no. 4. - Hungarian](#))

14. Magnetism I. Basic types of magnetism: paramagnets, diamagnets, ferromagnets (domains), examples; magnetization (M) and magnetic field (H), magnetic susceptibility; origin of atomic magnetic moments: Hund's rules.

(*S. H. Simon: The Oxford Solid State Basics, sections 19.1–19.2.*)

15. Magnetism II. Why do magnetic moments align? Investigation of a toy model (2 electrons in an atom), symmetry of the wavefunction, Pauli's exclusion principle, exchange energy; Simple models of magnetism: effective model of interacting spins (by Dirac), Heisenberg model, Ising model. Types of spontaneous magnetic order; ferromagnets, antiferromagnets, ferrimagnets; spontaneous symmetry breaking, frustration.

(*S. H. Simon: The Oxford Solid State Basics, section 19.2, chapter 20.*)

16. Magnetism III. The mean field theory of ferromagnets, effective (Weiss-)field, self consistency equation, stable and unstable solutions; paramagnetic and ferromagnetic phase, critical temperature (Curie-point); spontaneous magnetization as a function of temperature.

(*S. H. Simon: The Oxford Solid State Basics, chapter 22.*)

17. Introduction to superconductivity. Quantum mechanical basics: Schrödinger equation in \mathbf{A} -field, canonical and kinetic momentum, quantum mechanical current, probabilistic interpretation of wavefunction (Born); discovery of superconductivity, qualitative explanation of electron-electron attraction, Cooper pairs, Bose Einstein condensate, macroscopic wavefunction.

([The Feynman lectures on physics](#))

18. Superconductors in magnetic field. Persistent current, Meissner-effect, penetration depth of magnetic field, boundary condition for \mathbf{B} -field (image dipole), type I and type II superconductors, vortices and flux pinning (phenomenologically).

([The Feynman lectures on physics](#))